

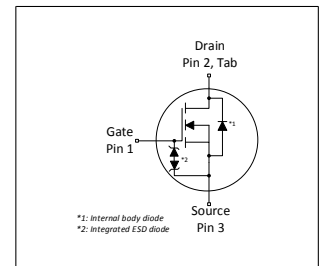
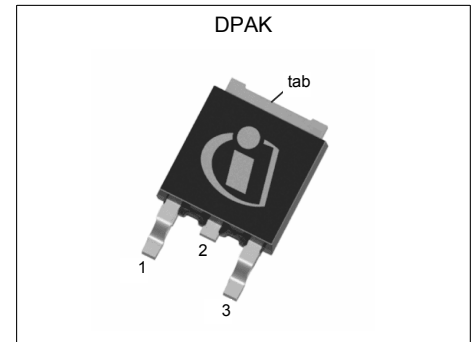
## MOSFET

### 600V CoolMOS™ PFD7 SJ Power Device

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

The latest CoolMOS™ PFD7 is an optimized platform tailored to target cost sensitive applications in consumer markets such as charger, adapter, motor drive, lighting, etc.

The new series provides all the benefits of a fast switching Superjunction MOSFET, combined with an excellent price/performance ratio and state of the art ease-of-use level. The technology meets highest efficiency standards and supports high power density, enabling customers going towards very slim designs.



### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $R_{DS(on)} \cdot E_{oss}$
- Low switching losses  $E_{oss}$ , excellent thermal behavior
- Fast body diode
- Wide range portfolio of  $R_{DS(on)}$  and package variations
- Integrated zener diode

### Benefits

- Enables high power density designs and small form factors
- Enables efficiency gains at higher switching frequencies
- Excellent commutation ruggedness
- Easy to select right parts and optimize the design
- High ESD ruggedness

### Potential applications

Recommended for ZVS topologies used in high density chargers, adapters, lighting and motor drives applications, etc.

### Product validation

Qualified according to JEDEC Standard

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*

**Table 1 Key Performance Parameters**

| Parameter            | Value | Unit |
|----------------------|-------|------|
| $V_{DS} @ T_{j,max}$ | 650   | V    |
| $R_{DS(on),max}$     | 2000  | mΩ   |
| $Q_{g,typ}$          | 3.8   | nC   |
| $I_{D,pulse}$        | 4.5   | A    |
| $E_{oss} @ 400V$     | 0.4   | μJ   |
| Body diode $di_F/dt$ | 1300  | A/μs |
| ESD Class (HBM)      | 2     | -    |

| Type / Ordering Code | Package     | Marking  | Related Links  |
|----------------------|-------------|----------|----------------|
| IPD60R2K0PFD7S       | PG-TO 252-3 | 60S2K0D7 | see Appendix A |

## Table of Contents

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## 1 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                      | Symbol        | Values |      |            | Unit             | Note / Test Condition                                                                         |
|------------------------------------------------|---------------|--------|------|------------|------------------|-----------------------------------------------------------------------------------------------|
|                                                |               | Min.   | Typ. | Max.       |                  |                                                                                               |
| Continuous drain current <sup>1)</sup>         | $I_D$         | -      | -    | 3.0<br>1.9 | A                | $T_C=25^\circ\text{C}$<br>$T_C=100^\circ\text{C}$                                             |
| Pulsed drain current <sup>2)</sup>             | $I_{D,pulse}$ | -      | -    | 4.5        | A                | $T_C=25^\circ\text{C}$                                                                        |
| Avalanche energy, single pulse                 | $E_{AS}$      | -      | -    | 5          | mJ               | $I_D=0.6\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10                                        |
| Avalanche energy, repetitive                   | $E_{AR}$      | -      | -    | 0.03       | mJ               | $I_D=0.6\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 10                                        |
| Avalanche current, single pulse                | $I_{AS}$      | -      | -    | 0.6        | A                | -                                                                                             |
| MOSFET dv/dt ruggedness                        | dv/dt         | -      | -    | 120        | V/ns             | $V_{DS}=0\dots400\text{V}$                                                                    |
| Gate source voltage (static)                   | $V_{GS}$      | -20    | -    | 20         | V                | static;                                                                                       |
| Gate source voltage (dynamic)                  | $V_{GS}$      | -30    | -    | 30         | V                | AC ( $f>1\text{ Hz}$ )                                                                        |
| Power dissipation                              | $P_{tot}$     | -      | -    | 20         | W                | $T_C=25^\circ\text{C}$                                                                        |
| Storage temperature                            | $T_{stg}$     | -40    | -    | 150        | $^\circ\text{C}$ | -                                                                                             |
| Operating junction temperature                 | $T_j$         | -40    | -    | 150        | $^\circ\text{C}$ | -                                                                                             |
| Mounting torque                                | -             | -      | -    | -          | Ncm              | -                                                                                             |
| Continuous diode forward current <sup>1)</sup> | $I_S$         | -      | -    | 3.0        | A                | $T_C=25^\circ\text{C}$                                                                        |
| Diode pulse current <sup>2)</sup>              | $I_{S,pulse}$ | -      | -    | 4.5        | A                | $T_C=25^\circ\text{C}$                                                                        |
| Reverse diode dv/dt <sup>3)</sup>              | dv/dt         | -      | -    | 70         | V/ns             | $V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 2.1\text{A}$ , $T_j=25^\circ\text{C}$<br>see table 8 |
| Maximum diode commutation speed                | di/dt         | -      | -    | 1300       | A/ $\mu\text{s}$ | $V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq 2.1\text{A}$ , $T_j=25^\circ\text{C}$<br>see table 8 |
| Insulation withstand voltage                   | $V_{ISO}$     | -      | -    | n.a.       | V                | $V_{rms}$ , $T_C=25^\circ\text{C}$ , $t=1\text{min}$                                          |

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum Duty Cycle  $D = 0.50$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_\theta$

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter                                              | Symbol     | Values |      |      | Unit | Note / Test Condition                                                                                                                                                               |
|--------------------------------------------------------|------------|--------|------|------|------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                                        |            | Min.   | Typ. | Max. |      |                                                                                                                                                                                     |
| Thermal resistance, junction - case                    | $R_{thJC}$ | -      | -    | 6.1  | °C/W | -                                                                                                                                                                                   |
| Thermal resistance, junction - ambient                 | $R_{thJA}$ | -      | -    | 62   | °C/W | device on PCB, minimal footprint                                                                                                                                                    |
| Thermal resistance, junction - ambient for SMD version | $R_{thJA}$ | -      | 35   | 45   | °C/W | Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm <sup>2</sup> (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling. |
| Soldering temperature, wave & reflow soldering allowed | $T_{sold}$ | -      | -    | 260  | °C   | reflow MSL3                                                                                                                                                                         |

### 3 Electrical characteristics

at  $T_j=25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

| Parameter                                     | Symbol        | Values |                |            | Unit     | Note / Test Condition                                                                             |
|-----------------------------------------------|---------------|--------|----------------|------------|----------|---------------------------------------------------------------------------------------------------|
|                                               |               | Min.   | Typ.           | Max.       |          |                                                                                                   |
| Drain-source breakdown voltage                | $V_{(BR)DSS}$ | 600    | -              | -          | V        | $V_{GS}=0V$ , $I_D=1mA$                                                                           |
| Gate threshold voltage                        | $V_{(GS)th}$  | 3.5    | 4              | 4.5        | V        | $V_{DS}=V_{GS}$ , $I_D=0.03mA$                                                                    |
| Zero gate voltage drain current <sup>1)</sup> | $I_{DSS}$     | -      | -              | 1          | $\mu A$  | $V_{DS}=600V$ , $V_{GS}=0V$ , $T_j=25^\circ C$<br>$V_{DS}=600V$ , $V_{GS}=0V$ , $T_j=125^\circ C$ |
| Gate-source leakage current                   | $I_{GSS}$     | -      | -              | 1000       | nA       | $V_{GS}=20V$ , $V_{DS}=0V$                                                                        |
| Drain-source on-state resistance              | $R_{DS(on)}$  | -      | 1.626<br>3.824 | 2.000<br>- | $\Omega$ | $V_{GS}=10V$ , $I_D=0.5A$ , $T_j=25^\circ C$<br>$V_{GS}=10V$ , $I_D=0.5A$ , $T_j=150^\circ C$     |
| Gate resistance                               | $R_G$         | -      | 11.0           | -          | $\Omega$ | $f=1MHz$ , open drain                                                                             |

**Table 5 Dynamic characteristics**

| Parameter                                                  | Symbol       | Values |      |      | Unit | Note / Test Condition                                                         |
|------------------------------------------------------------|--------------|--------|------|------|------|-------------------------------------------------------------------------------|
|                                                            |              | Min.   | Typ. | Max. |      |                                                                               |
| Input capacitance                                          | $C_{iss}$    | -      | 134  | -    | pF   | $V_{GS}=0V$ , $V_{DS}=400V$ , $f=250kHz$                                      |
| Output capacitance                                         | $C_{oss}$    | -      | 3    | -    | pF   | $V_{GS}=0V$ , $V_{DS}=400V$ , $f=250kHz$                                      |
| Effective output capacitance, energy related <sup>2)</sup> | $C_{o(er)}$  | -      | 5    | -    | pF   | $V_{GS}=0V$ , $V_{DS}=0...400V$                                               |
| Effective output capacitance, time related <sup>3)</sup>   | $C_{o(tr)}$  | -      | 47   | -    | pF   | $I_D=constant$ , $V_{GS}=0V$ , $V_{DS}=0...400V$                              |
| Turn-on delay time                                         | $t_{d(on)}$  | -      | 5.5  | -    | ns   | $V_{DD}=400V$ , $V_{GS}=10V$ , $I_D=0.5A$ ,<br>$R_G=10.2\Omega$ ; see table 9 |
| Rise time                                                  | $t_r$        | -      | 7.2  | -    | ns   | $V_{DD}=400V$ , $V_{GS}=10V$ , $I_D=0.5A$ ,<br>$R_G=10.2\Omega$ ; see table 9 |
| Turn-off delay time                                        | $t_{d(off)}$ | -      | 41   | -    | ns   | $V_{DD}=400V$ , $V_{GS}=10V$ , $I_D=0.5A$ ,<br>$R_G=10.2\Omega$ ; see table 9 |
| Fall time                                                  | $t_f$        | -      | 105  | -    | ns   | $V_{DD}=400V$ , $V_{GS}=10V$ , $I_D=0.5A$ ,<br>$R_G=10.2\Omega$ ; see table 9 |

**Table 6 Gate charge characteristics**

| Parameter             | Symbol        | Values |      |      | Unit | Note / Test Condition                            |
|-----------------------|---------------|--------|------|------|------|--------------------------------------------------|
|                       |               | Min.   | Typ. | Max. |      |                                                  |
| Gate to source charge | $Q_{gs}$      | -      | 0.8  | -    | nC   | $V_{DD}=400V$ , $I_D=0.5A$ , $V_{GS}=0$ to $10V$ |
| Gate to drain charge  | $Q_{gd}$      | -      | 1.5  | -    | nC   | $V_{DD}=400V$ , $I_D=0.5A$ , $V_{GS}=0$ to $10V$ |
| Gate charge total     | $Q_g$         | -      | 3.8  | -    | nC   | $V_{DD}=400V$ , $I_D=0.5A$ , $V_{GS}=0$ to $10V$ |
| Gate plateau voltage  | $V_{plateau}$ | -      | 5.6  | -    | V    | $V_{DD}=400V$ , $I_D=0.5A$ , $V_{GS}=0$ to $10V$ |

<sup>1)</sup> Maximum specification is defined by calculated six sigma upper confidence bound

<sup>2)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

<sup>3)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

**Table 7 Reverse diode characteristics**

| Parameter                     | Symbol    | Values |      |      | Unit    | Note / Test Condition                                        |
|-------------------------------|-----------|--------|------|------|---------|--------------------------------------------------------------|
|                               |           | Min.   | Typ. | Max. |         |                                                              |
| Diode forward voltage         | $V_{SD}$  | -      | 1.0  | -    | V       | $V_{GS}=0V$ , $I_F=0.5A$ , $T_j=25^{\circ}C$                 |
| Reverse recovery time         | $t_{rr}$  | -      | 34   | 51   | ns      | $V_R=400V$ , $I_F=0.5A$ , $di_F/dt=100A/\mu s$ ; see table 8 |
| Reverse recovery charge       | $Q_{rr}$  | -      | 0.05 | 0.10 | $\mu C$ | $V_R=400V$ , $I_F=0.5A$ , $di_F/dt=100A/\mu s$ ; see table 8 |
| Peak reverse recovery current | $I_{rrm}$ | -      | 2.5  | -    | A       | $V_R=400V$ , $I_F=0.5A$ , $di_F/dt=100A/\mu s$ ; see table 8 |

## 4 Electrical characteristics diagrams

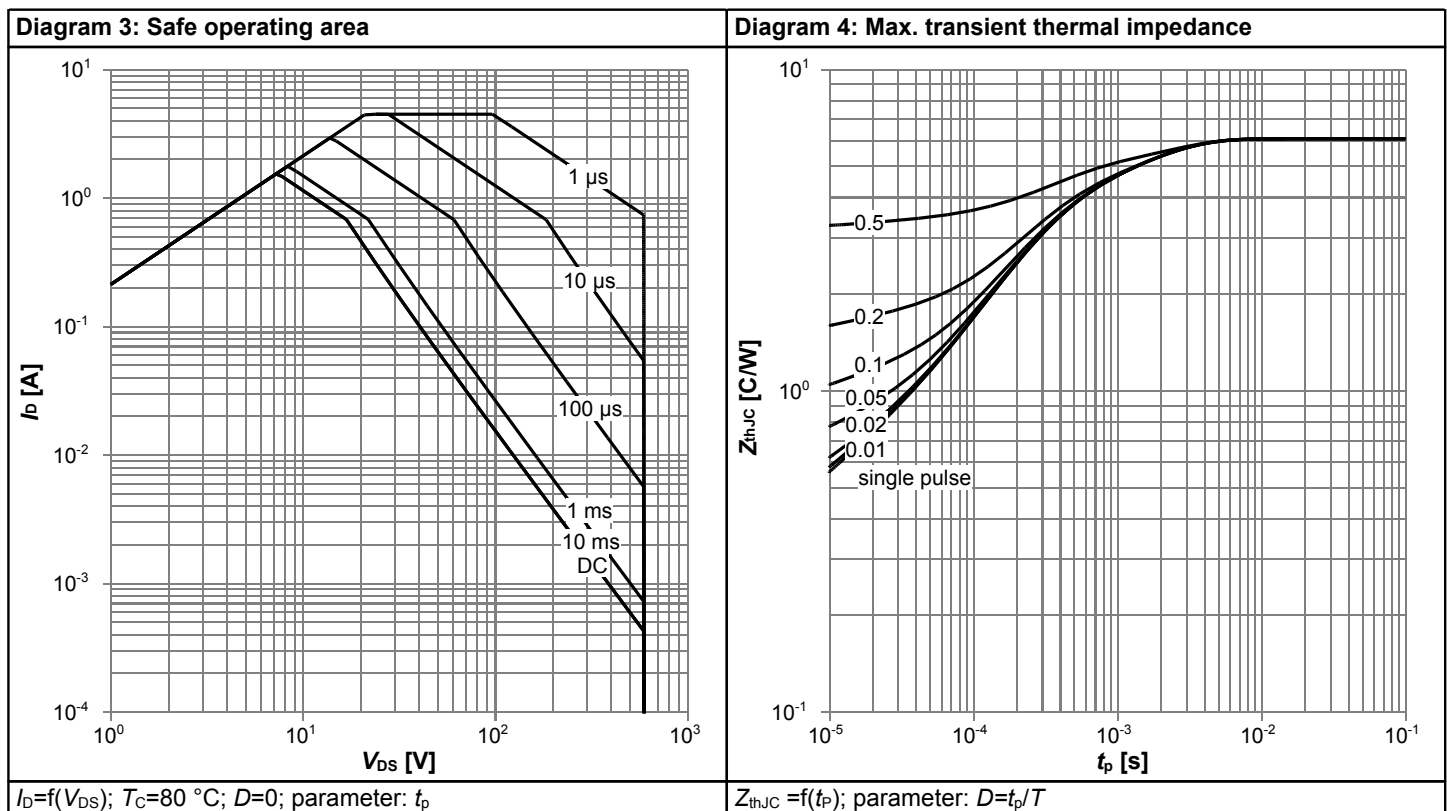
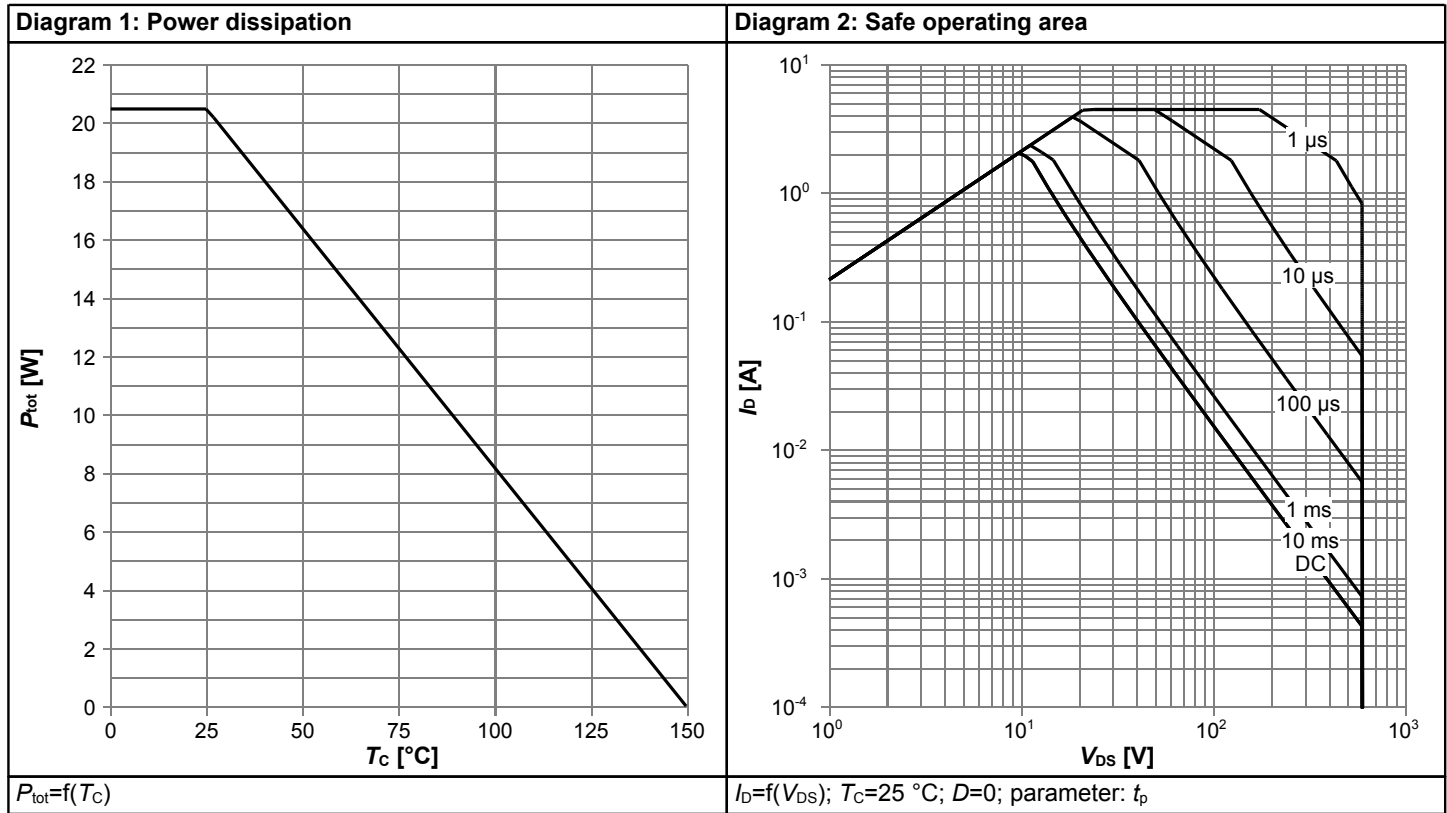
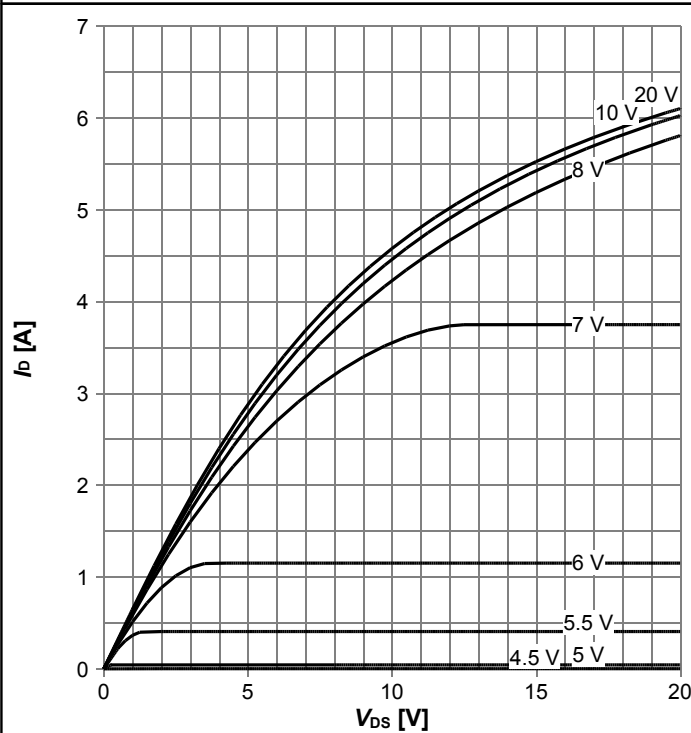
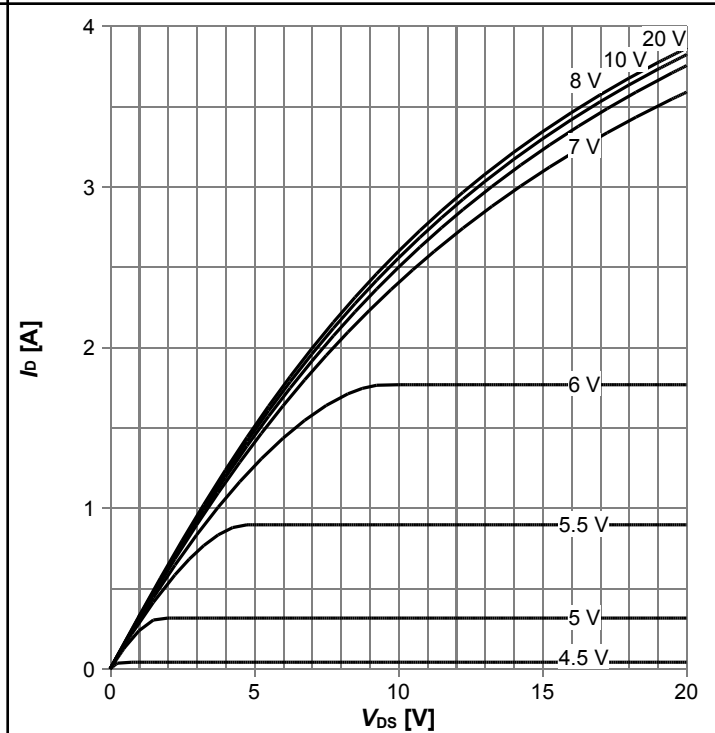


Diagram 5: Typ. output characteristics



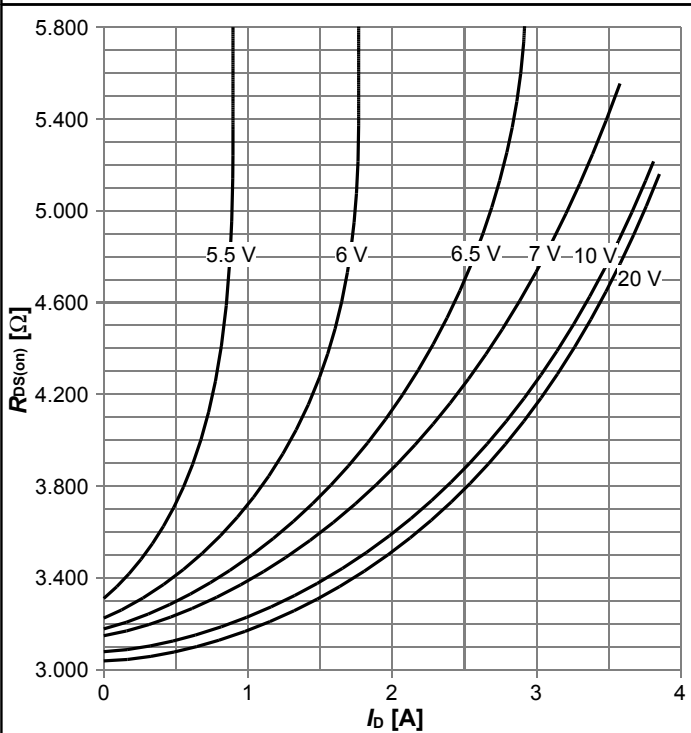
$I_D = f(V_{DS})$ ;  $T_J = 25\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. output characteristics



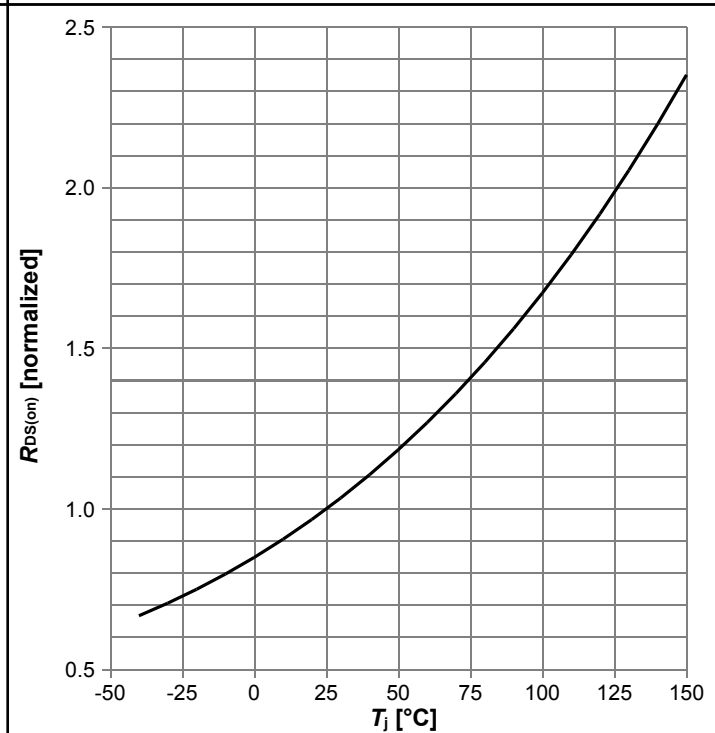
$I_D = f(V_{DS})$ ;  $T_J = 125\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)} = f(I_D)$ ;  $T_J = 125\text{ °C}$ ; parameter:  $V_{GS}$

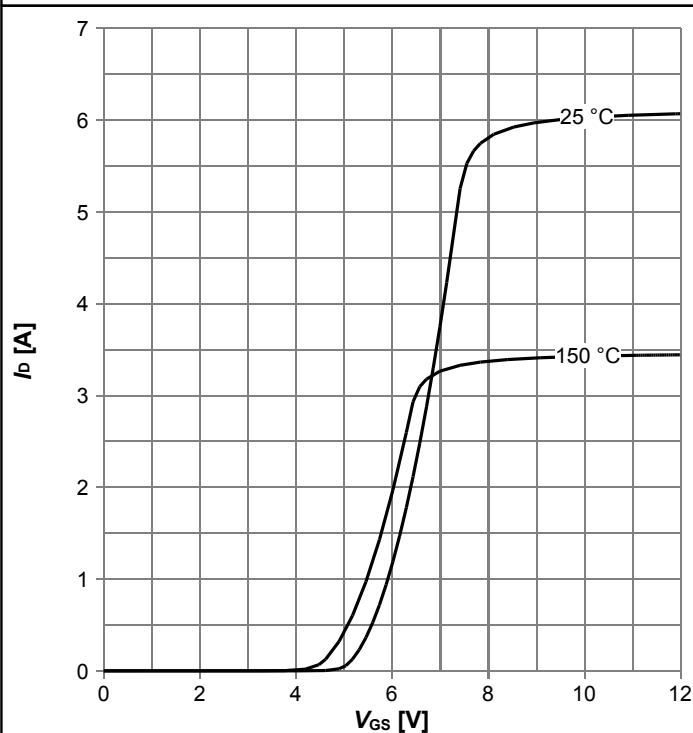
Diagram 8: Drain-source on-state resistance



$R_{DS(on)} = f(T_J)$ ;  $I_D = 0.5\text{ A}$ ;  $V_{GS} = 10\text{ V}$

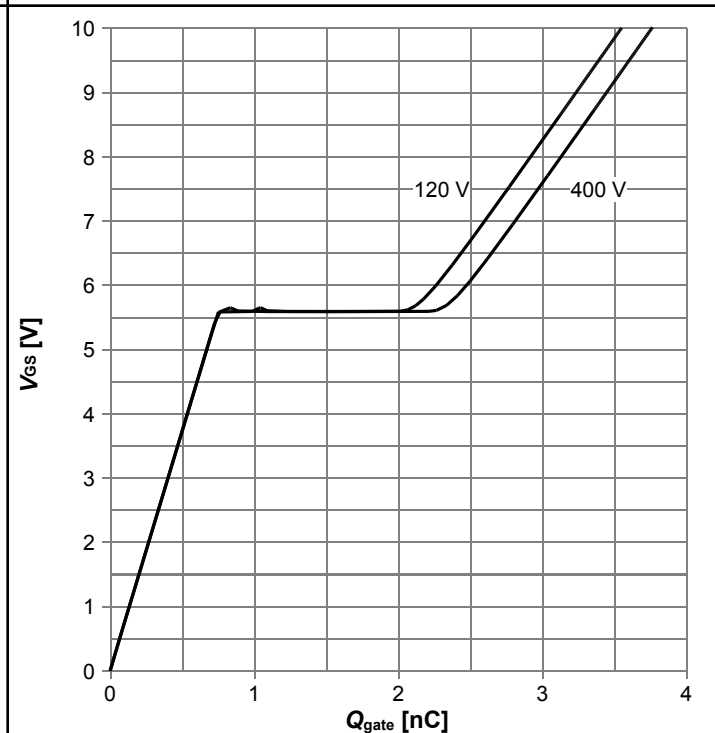


**Diagram 9: Typ. transfer characteristics**



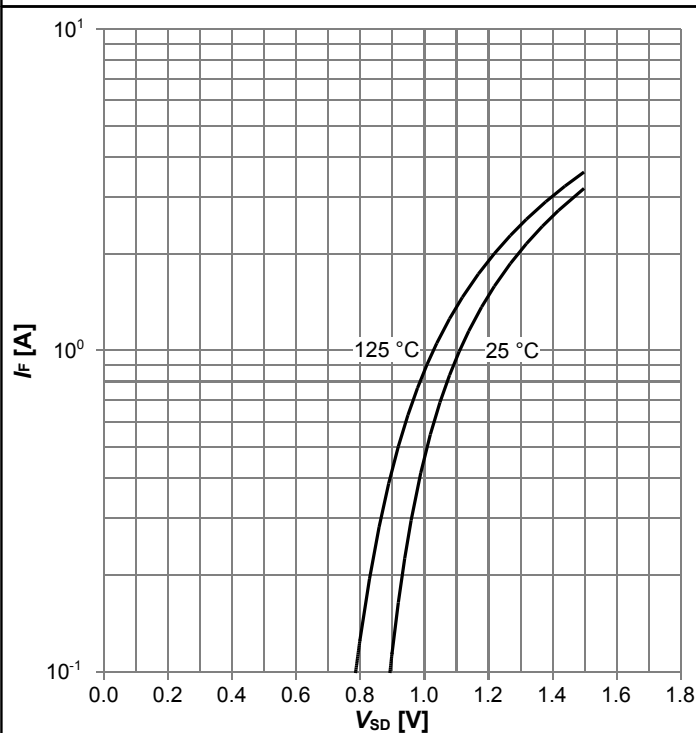
$I_D = f(V_{GS})$ ;  $V_{DS} = 20V$ ; parameter:  $T_j$

**Diagram 10: Typ. gate charge**



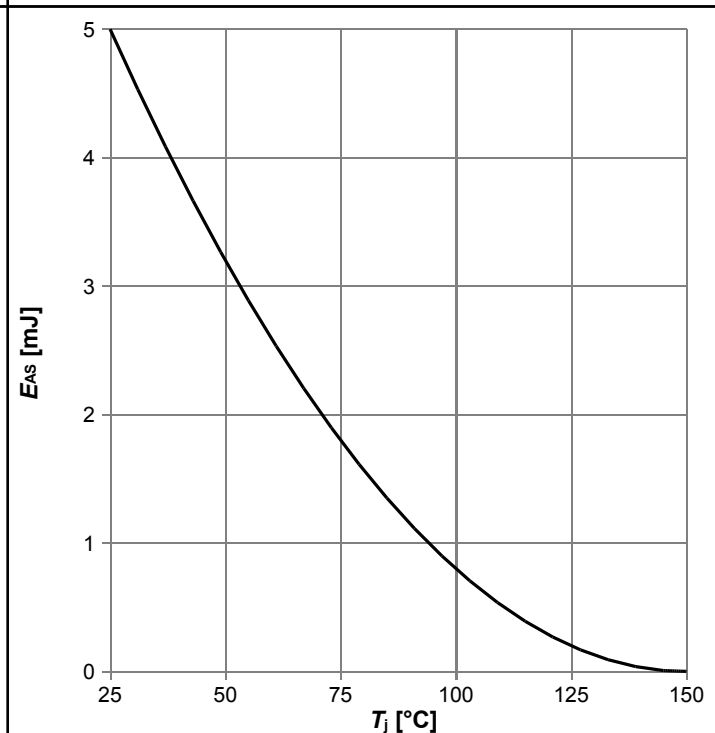
$V_{GS} = f(Q_{gate})$ ;  $I_D = 0.5$  A pulsed; parameter:  $V_{DD}$

**Diagram 11: Forward characteristics of reverse diode**



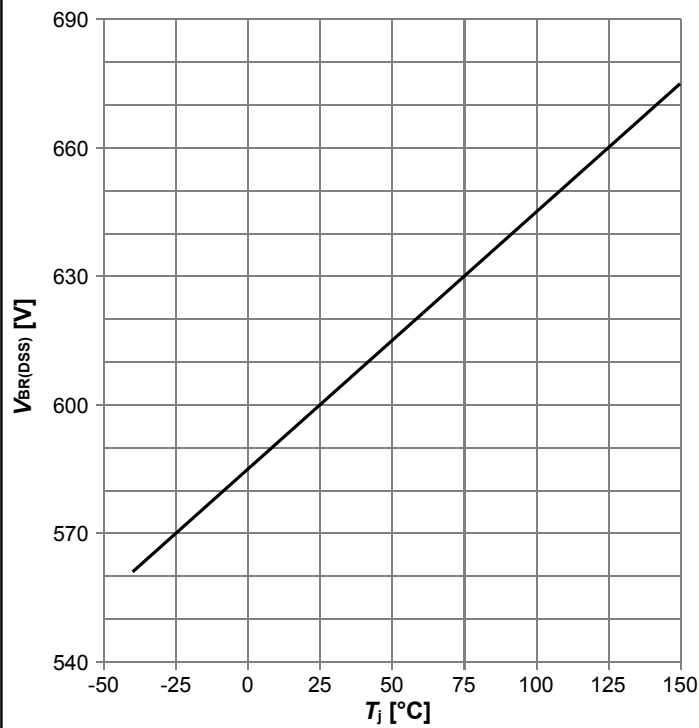
$I_F = f(V_{SD})$ ; parameter:  $T_j$

**Diagram 12: Avalanche energy**



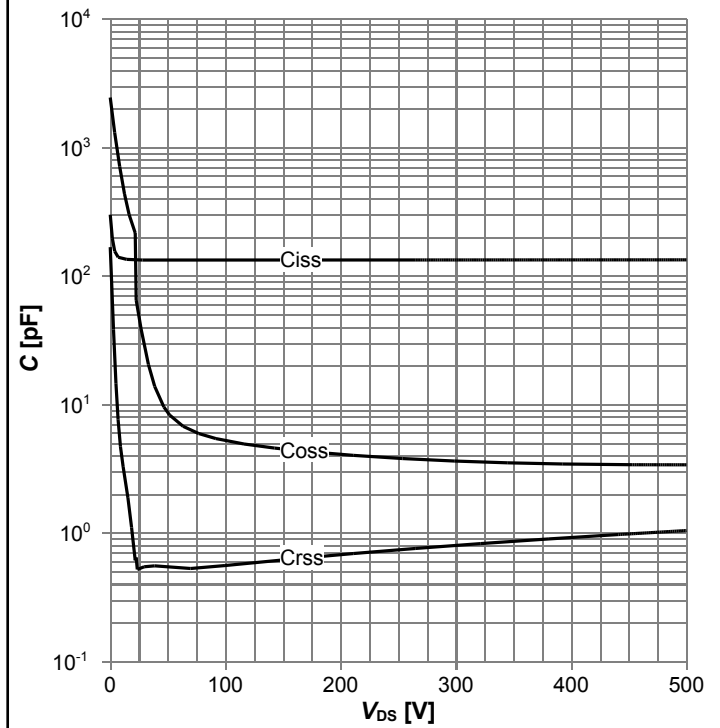
$E_{AS} = f(T_j)$ ;  $I_D = 0.6$  A;  $V_{DD} = 50$  V

**Diagram 13: Drain-source breakdown voltage**



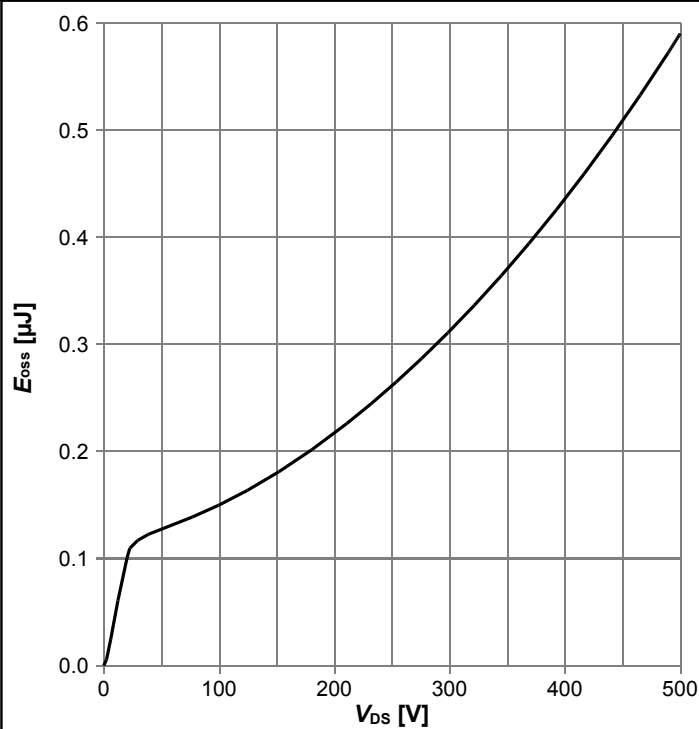
$V_{BR(DSS)} = f(T_J); I_D = 1 \text{ mA}$

**Diagram 14: Typ. capacitances**



$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$

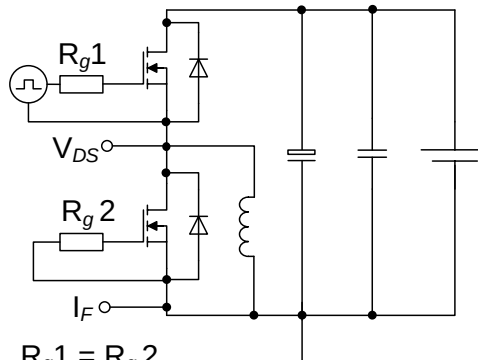
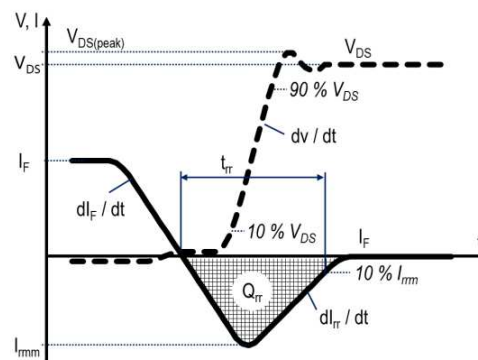
**Diagram 15: Typ. Coss stored energy**



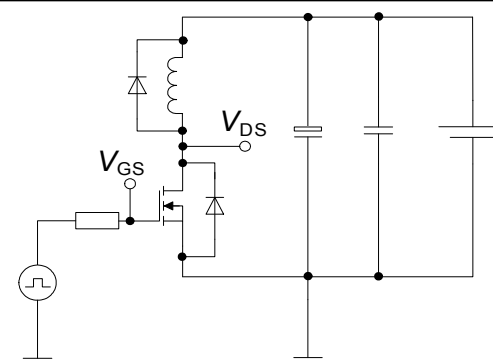
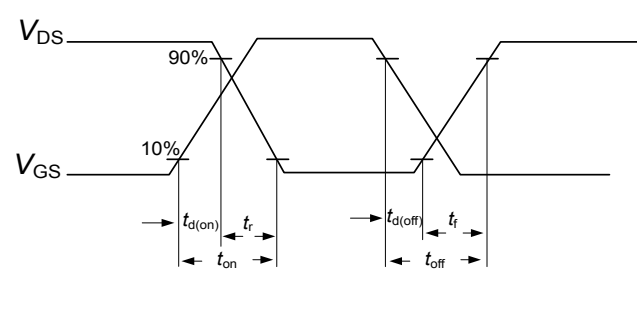
$E_{oss} = f(V_{DS})$

## 5 Test Circuits

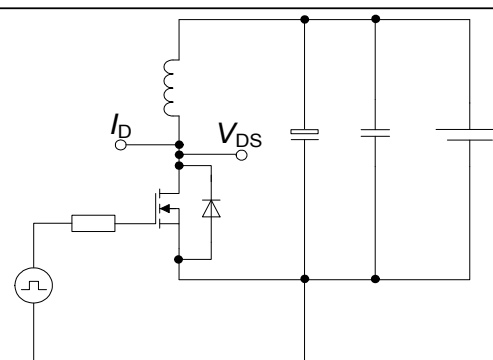
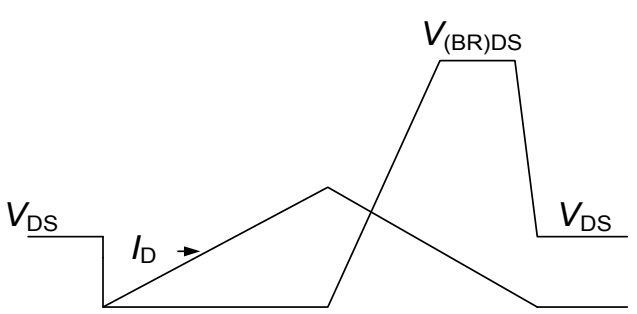
**Table 8 Diode characteristics**

| Test circuit for diode characteristics                                                                                | Diode recovery waveform                                                            |
|-----------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------|
|  <p><math>R_{g1} = R_{g2}</math></p> |  |

**Table 9 Switching times**

| Switching times test circuit for inductive load                                    | Switching times waveform                                                            |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |

**Table 10 Unclamped inductive load**

| Unclamped inductive load test circuit                                               | Unclamped inductive waveform                                                         |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |

## 6 Package Outlines

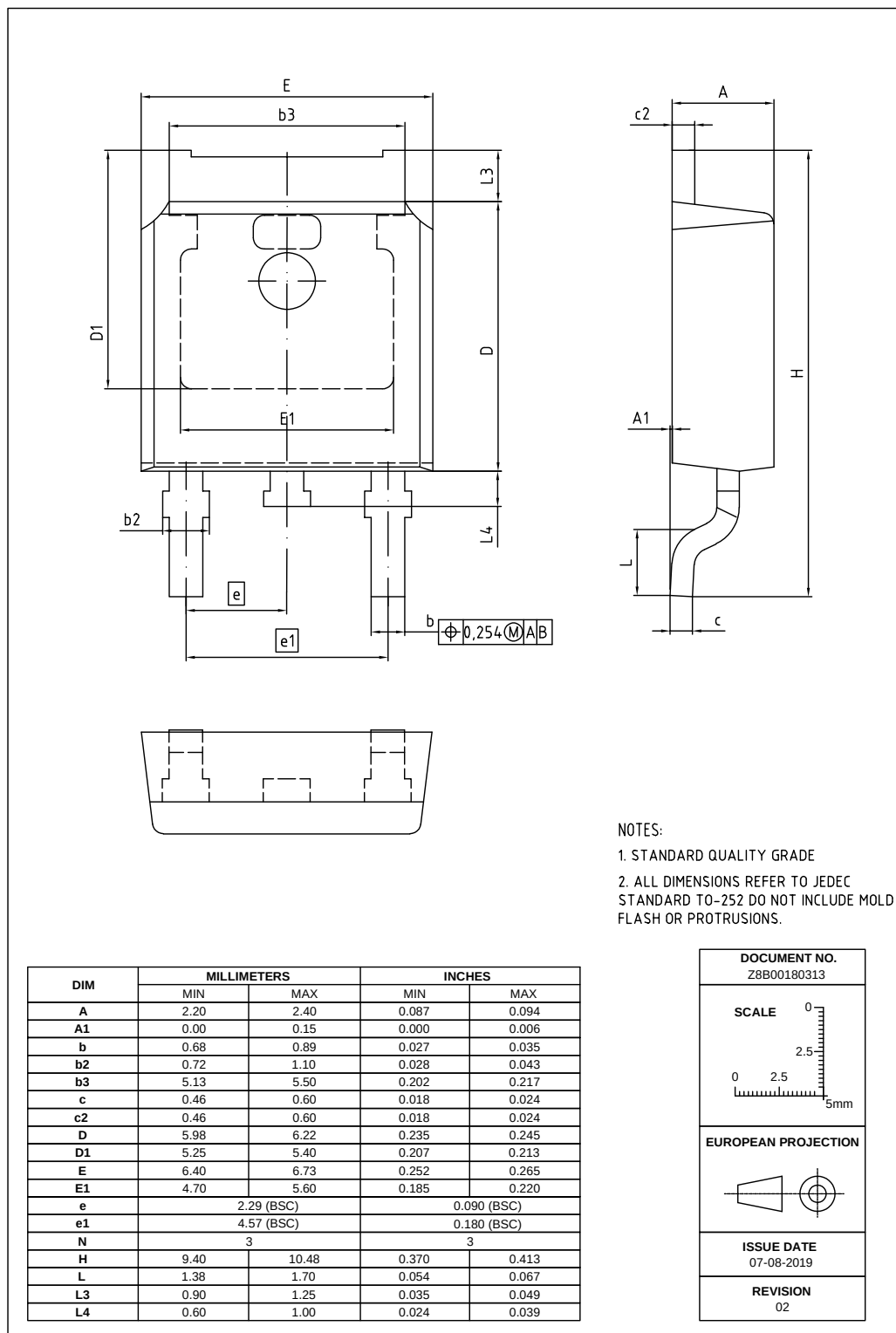


Figure 1 Outline PG-TO 252-3, dimensions in mm/inches

## **7 Appendix A**

### **Table 11 Related Links**

- **IFX CoolMOS PFD7 Webpage:** [www.infineon.com](http://www.infineon.com)
- **IFX CoolMOS PFD7 application note:** [www.infineon.com](http://www.infineon.com)
- **IFX CoolMOS PFD7 simulation model:** [www.infineon.com](http://www.infineon.com)
- **IFX Design tools:** [www.infineon.com](http://www.infineon.com)

## Revision History

IPD60R2K0PFD7S

**Revision: 2019-09-27, Rev. 2.0**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 2.0      | 2019-09-27 | Release of final version                     |

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